

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
18 November 2004 (18.11.2004)

PCT

(10) International Publication Number
WO 2004/100252 A1

(51) International Patent Classification⁷: **H01L 21/68**

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(21) International Application Number:
PCT/AU2004/000594

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(22) International Filing Date: 7 May 2004 (07.05.2004)

(25) Filing Language: English

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(26) Publication Language: English

(30) Priority Data:
2003902270 9 May 2003 (09.05.2003) AU

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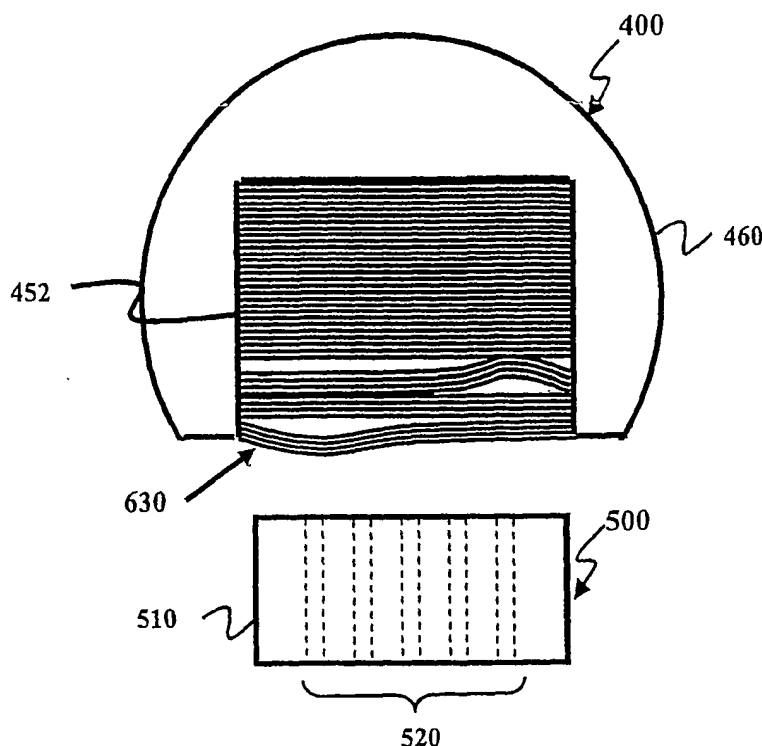
(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,

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[Continued on next page]

(54) Title: SEPARATING AND ASSEMBLING SEMICONDUCTOR STRIPS



(57) Abstract: A method and an apparatus for separating elongated semiconductor strips (630) from a wafer (400) of semiconductor material are disclosed. Vacuum (500) is applied to the face of each semiconductor strip forming an edge of the wafer (400) or being adjacent to the edge. The wafer (400) and the source of the vacuum (500) are displaced to separate each elongated semiconductor strip (630) from the wafer (400). Further, a method and an apparatus for assembling elongated semiconductor strips (630) separated from a wafer (400) of semiconductor material into an array of strips (630) are disclosed. Still further, methods, apparatuses, and systems for assembling an array of elongated semiconductor strips (630) on a substrate are also disclosed.

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SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

— *with international search report*